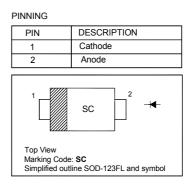
Surface Mount Schottky Barrier Diode

Features

- Very low forward voltage
- High Current Capability



Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RRM}	20	V
Working Peak Reverse Voltage	V _{RWM}	20	V
DC Reverse Voltage	V _R	20	V
Average Rectified Forward Current	I _{F(AV)}	0.5	А
Peak Forward Surge Current (8.3 ms Single Half Sine-wave)	I _{FSM}	20	А
Thermal Resistance Junction to Ambient	$R_{ extsf{ heta}JA}$	340	°C/W
Thermal Resistance Junction to Lead	$R_{ extsf{ heta}JL}$	150	°C/W
Junction Temperature	Tj	- 65 to + 150	°C
Storage Temperature	T _{stg}	- 65 to + 150	°C

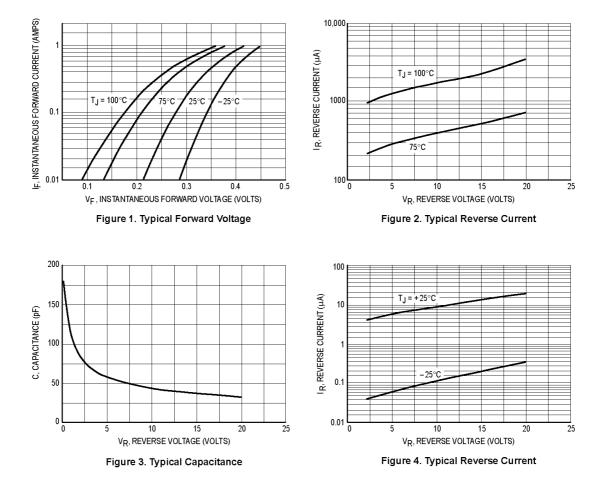
 $^{1)}$ Following any rated load condition and with rated V_{RRM} applied.

Characteristics at T_a = 25°C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.1 \text{ A}$, $T_j = 25^{\circ}\text{C}$ at $I_F = 0.5 \text{ A}$, $T_j = 25^{\circ}\text{C}$ at $I_F = 0.1 \text{ A}$, $T_j = 100^{\circ}\text{C}$ at $I_F = 0.5 \text{ A}$, $T_j = 100^{\circ}\text{C}$	V _F	0.375 0.44 0.26 0.36	V
Reverse Current at $V_R = 10 \text{ V}, T_j = 25^{\circ}\text{C}$ at $V_R = 20 \text{ V}, T_j = 25^{\circ}\text{C}$ at $V_R = 10 \text{ V}, T_j = 100^{\circ}\text{C}$ at $V_R = 20 \text{ V}, T_j = 100^{\circ}\text{C}$	I _R	40 150 3 7	μA μA mA mA
Total Capacitance at V _R = 5 V (test signal range 100 KHz to 1 MHz), T _j = 25 °C	C _{tot}	110	pF



TOP DYNAMIC





TOP DYNAMIC

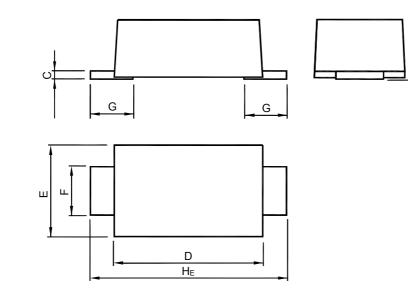
Dated: 13/07/2015 Rev: 04

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

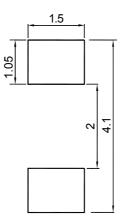
SOD-123FL

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UNIT	А	В	С	D	E	F	G	H _E
mm	1.08	0.1	0.2	2.9	1.9	1.1	0.9	3.9
	0.88	0	0.1	2.6	1.7	0.8	0.7	3.5

Recommended Soldering Footprint



Packing information

Package Tape Width		Pitch		Reel Size		Per Reel Packing Quantity
гаскауе	(mm)	mm	inch	mm	inch	Fel Reel Facking Quantity
SOD-123FL	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000



TOP DYNAMIC